



FZT958

### 400V PNP MEDIUM POWER TRANSISTOR IN SOT223

### **Features**

- BV<sub>CEO</sub> > -400V
- I<sub>C</sub> = -0.5A High Continuous Collector Current
- I<sub>CM</sub> = -1.5A Peak Pulse Current
- Low Saturation Voltage V<sub>CE(SAT)</sub> < -400mV @ -0.5A</li>
- hFE Specified up to -2A for a High Gain Hold-Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

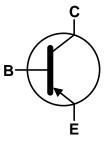
### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202. Method 208 <sup>(3)</sup>
- Weight: 0.112 grams (Approximate)

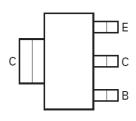




Top View



Device Symbol



Top View Pin-Out

### Ordering Information (Note 4)

Part Number	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity Per Reel
FZT958TA	AEC-Q101	FZT958	7	12	1,000

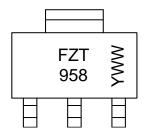
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.

- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

### **Marking Information**

Notes:

SOT223



FZT 958 = Product Type Marking Code YWW = Date Code Marking Y or  $\overline{Y}$  = Last Digit of Year (ex: 6 = 2016) WW or  $\overline{W}W$  = Week Code (01 to 53)



## Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	-400	V
Collector-Emitter Voltage	$V_{\sf CEO}$	-400	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-0.5	Α
Peak Pulse Current	Ісм	-1.5	Α

## Thermal Characteristics ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	0	3.0 24	W mW/°C	
Linear Derating Factor	(Note 6)	P <sub>D</sub>	1.6 12.8		
Thermal Decistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ hetaJL}$	8.8		
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	8,000	V	3B
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

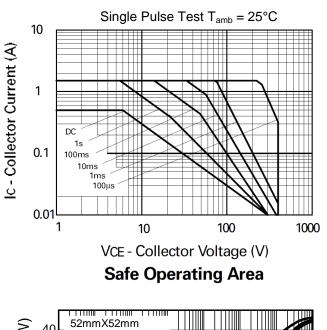
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in steady-state.

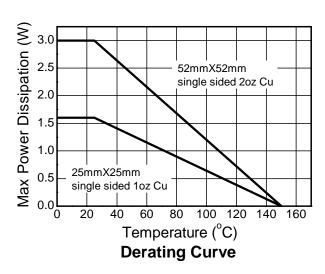
  6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).

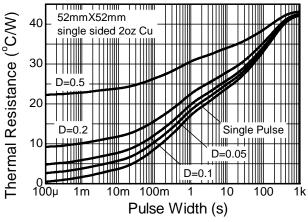
  8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

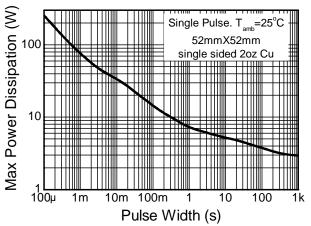


## **Thermal Characteristics and Derating Information**









**Transient Thermal Impedance** 

**Pulse Power Dissipation** 



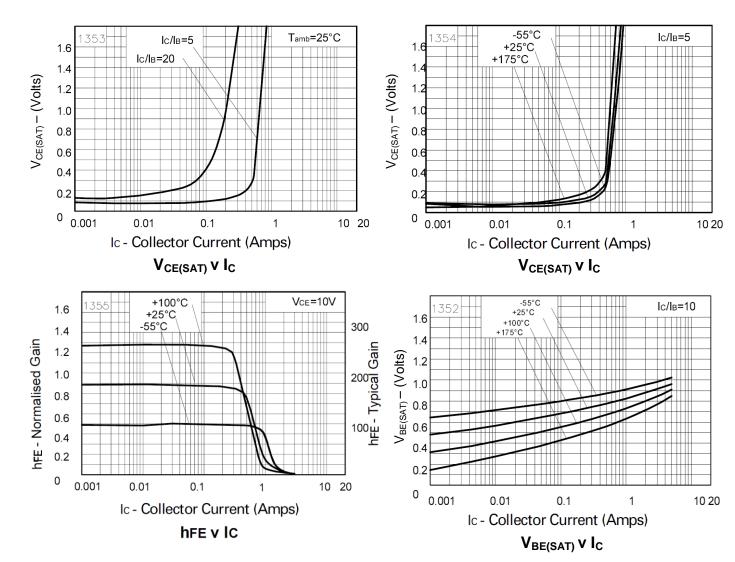
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

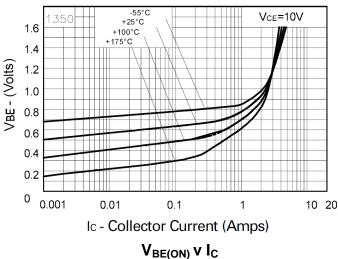
Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-400	-600	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	-400	-600	_	V	$I_C = -1\mu A, R_B \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	-400	-550	_	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-7	-8	_	V	I <sub>E</sub> = -100μA
Collector Cut-Off Current		_	<1	-50	nA	V <sub>CB</sub> = -300V
Collector Cut-On Current	I <sub>CBO</sub>	_	_	-1	μΑ	$V_{CB} = -300V, T_A = +100$ °C
		_	<1	-50	nA	$V_{CE} = -300V, R \le 1k\Omega$
Collector Cut-Off Current	I <sub>CER</sub>	_	_	-1	μA	$V_{CE}$ = -300V, R $\leq$ 1k $\Omega$ , T <sub>A</sub> = +100°C
Emitter Cut-Off Current	I <sub>EBO</sub>	_	<1	-10	nA	V <sub>EB</sub> = -6V
		100	200	_	_	I <sub>C</sub> = -10mA, V <sub>CE</sub> = -10V
DC Current Transfer Static Ratio (Note 9)	h <sub>FE</sub>	100	200	300		$I_C = -0.5A$ , $V_{CE} = -10V$
		10	20	_		I <sub>C</sub> = -1A, V <sub>CE</sub> = -10V
		_	-100	-150		$I_C = -10mA, I_B = -1mA$
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(SAT)</sub>	_	-150	-200	mV	$I_C = -100 \text{mA}, I_B = -10 \text{mA}$
	, ,	_	-340	-400		$I_C = -500 \text{mA}, I_B = -100 \text{mA}$
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(SAT)</sub>	_	-830	-950	mV	$I_C = -0.5A$ , $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(ON)</sub>	_	-725	-840	mV	$I_C = -0.5A, V_{CE} = -10V$
Transitional Frequency	f <sub>T</sub>	_	85	_	MHz	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -10V, f = 50MHz
Output Capacitance	Сово	_	19	_	pF	V <sub>CB</sub> = -20V, f = 1MHz
Switching Time	t <sub>ON</sub>	_	104	-	no	$V_{CC} = -100V, I_{C} = -500mA,$
Switching Time	toff	_	2,400	-	ns	$I_{B1} = -I_{B2} = -50 \text{mA}$

Note: 9. Measured under pulsed conditions. Pulse width  $\leq 300 \mu s$ . Duty cycle  $\leq 2\%$ .



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)



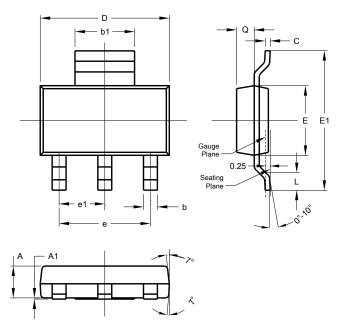




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT223**

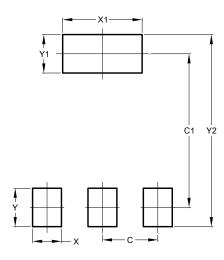


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### **SOT223**



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.



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